# **N-Channel General-Purpose Amplifier**

# MMBFJ201, MMBFJ202

#### Description

This device is designed primarily for low level audio and general-purpose applications with high impedance signal sources. Sourced from process 52.

#### Applications

• These are Pb-Free Devices

**ABSOLUTE MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$  unless otherwise noted) (Note 1, 2)

Symbol	Parameter	Value	Unit	
V <sub>DG</sub> Drain-Gate Voltage		40	V	
V <sub>GS</sub> Gate-Source Voltage		-40	V	
I <sub>GF</sub>	I <sub>GF</sub> Forward Gate Current		mA	
T <sub>J</sub> , T <sub>STG</sub> Operating and Storage Junction Temperature Range		–55 to 150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. These ratings are based on a maximum junction temperature of 150°C. 2. These are steady-state limits. ON Semiconductor should be consulted on

applications involving pulsed or low-duty-cycle operations.

THERMAL	_ CHARAO	CTERISTICS	$(T_A = 25^{\circ}C \text{ unless otherwise r})$	oted)
(Note 3)				
	_			

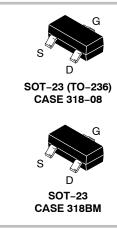
	Symbol	Parameter	Max	Unit
P <sub>D</sub> Total Device Dissipation		Total Device Dissipation	350	mW
		Derate Above 25°C	2.8	mW/°C
	$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient	357	°C/W

3. Device mounted on FR-4 PCB 36 mm x 18 mm x 1.5 mm; mounting pad for the collector lead minimum 6 cm<sup>2</sup>.

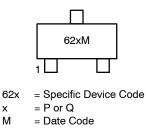


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#### MARKING DIAGRAMS



#### **ORDERING INFORMATION**

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See detailed ordering and shipping information on page 5 of this data sheet.

#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Test Condition		Max	Unit
OFF CHARACTERISTICS						
V <sub>(BR)GSS</sub>	Gate-Source Breakdown Voltage	$I_{G} = -1.0 \ \mu A, \ V_{DS} = 0$		-40	-	V
I <sub>GSS</sub>	Gate Reverse Current	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0$		-	-100	pА
V <sub>GS</sub> (off)	Gate-Source Cut-Off Voltage	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 10 \text{ nA}$	MMBFJ201	-0.3	-1.5	V
			MMBFJ202	-0.8	-4.0	

#### **ON CHARACTERISTICS**

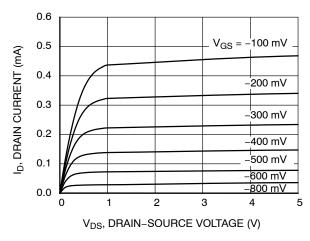
I <sub>DSS</sub>	Zero-Gate Voltage Drain Current (Note 4)	$V_{DS} = 20 \text{ V}, \text{ I}_{GS} = 0$	MMBFJ201	0.2	1.0	mA
			MMBFJ202	0.9	4.5	

#### SMALL SIGNAL CHARACTERISTICS

УFS	Forward Transfer Admittance	$V_{DS}$ = 20 V, f = 1.0 kHz	MMBFJ201	500	μmhos	Ī
			MMBFJ202	1000	1	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulse test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%.

#### **TYPICAL PERFORMANCE CHARACTERISTICS**





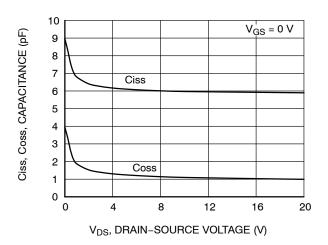


Figure 3. Capacitance vs. Voltage (MMBJF201)

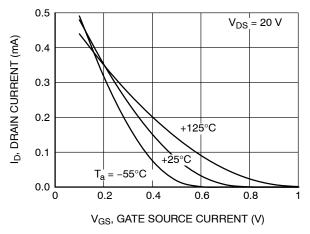


Figure 5. Transfer Characteristics (MMBFJ201)

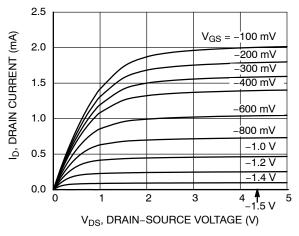


Figure 2. Common Drain-Source (MMBJF202)

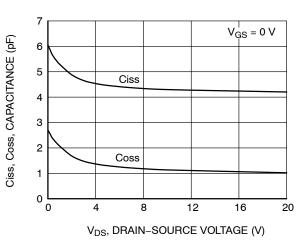


Figure 4. Capacitance vs. Voltage (MMBJF202)

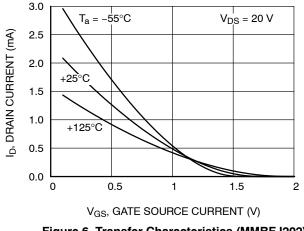
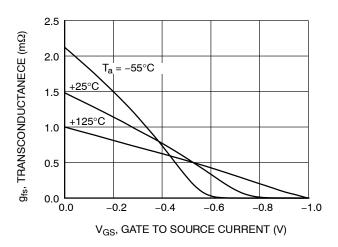


Figure 6. Transfer Characteristics (MMBFJ202)

#### TYPICAL PERFORMANCE CHARACTERISTICS (Continued)





MMBFJ202

MMBFJ201

20

 $T_a = +25^{\circ}C$ 

60

10000

1000

100

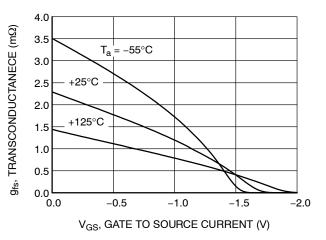
10

1

0,1

0,01 L 0

I<sub>GSS</sub>, GATE LEAKAGE CURRENT (nA)





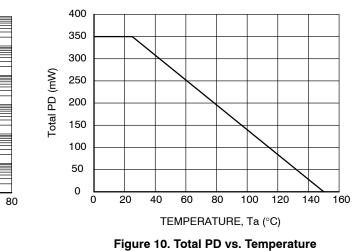


Figure 9. Leakage Current vs. Voltage

40

V<sub>DG</sub> (V)

#### **ORDERING INFORMATION**

Part Number	Top Mark	Package	Shipping <sup>†</sup>
MMBFJ201	62P	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBFJ202 62Q		SOT-23 (TO-236) (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





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